

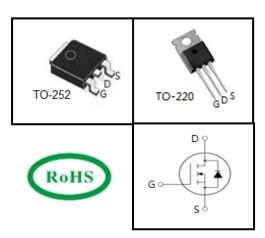
# **40V N-Channel Trench MOSFET**

# FEATURES

- Trench Power MOSFET Technology
- Low R<sub>DS(ON)</sub>
- Low Gate Charge
- Optimized For Fast-switching Applications

# APPLICATIONS

- Synchronous Rectification in DC/DC and AC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial



Device Marking and Package Information			
Device	vice Package		
TTD120N04AT	TO-252	120N04AT	
TTP120N04AT	TO-220	120N04AT	

<b>Absolute Maximum Ratings</b> $T_c = 25^{\circ}C$ , unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage (V <sub>GS</sub> = 0V)	V <sub>DSS</sub>	40	V
Continuous Drain Current	I <sub>D</sub>	120	А
Pulsed Drain Current (note1)	I <sub>DM</sub>	480	А
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Single Pulse Avalanche Energy (note2)	E <sub>AS</sub>	138.4	mJ
Avalanche Current	I <sub>As</sub>	35	A
Power Dissipation ( $T_c = 25^{\circ}C$ )	P <sub>D</sub>	143	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55~+175	°C

Thermal Resistance			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R <sub>thJC</sub>	1.05	
Thermal Resistance, Junction-to-Ambient	R <sub>thJA</sub>	60	K/W



<b>Specifications</b> $T_J = 25^{\circ}C$ , ur	less othe	rwise noted				
Parameter	Symbol	Test Osnalitions	Value			l lusit
		Test Conditions	Min.	Тур.	Max.	Unit
Static				-		
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0V, I_{D} = 250\mu A$	40			V
Zara Cata Valtaga Drain Currant	I	$V_{DS} = 40V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 40V, V_{GS} = 0V, T_{J} = 150^{\circ}C$			100	μA
Gate-Source Leakage	I <sub>GSS</sub>	$V_{GS}$ = $\pm 20V$			±100	nA
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.0	1.7	2.4	V
Drain October On Desistance (Nata)	D	V <sub>GS</sub> = 10V, I <sub>D</sub> = 30A		2.7	3.5	mΩ
Drain-Source On-Resistance (Note3)	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 30A		3.6	4.7	mΩ
Forward Transconductance (Note3)	<b>g</b> <sub>fs</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> =20A		45.5		S
Dynamic						
Input Capacitance	C <sub>iss</sub>	$\mathcal{M} = \mathcal{O}\mathcal{M}$		10179		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0V,$ $V_{DS} = 20V,$		587		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1.0MHz		439		
Total Gate Charge	Qg	$V_{DD} = 20V, I_{D} = 20A,$ $V_{GS} = 10V$		132		
Gate-Source Charge	Q <sub>gs</sub>			23		nC
Gate-Drain Charge	$Q_{gd}$	65		23		
Turn-on Delay Time	t <sub>d(on)</sub>			27		
Turn-on Rise Time	t <sub>r</sub>	V <sub>DD</sub> = 20V, I <sub>D</sub> = 20A,		11		
Turn-off Delay Time	t <sub>d(off)</sub>	$R_{G} = 3\Omega$		83		ns
Turn-off Fall Time	t <sub>f</sub>			14		1
Drain-Source Body Diode Characteris	stics					
Continuous Body Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25°C			120	•
Pulsed Diode Forward Current	I <sub>SM</sub>				480	A
Body Diode Voltage	V <sub>SD</sub>	$T_J = 25^{\circ}C, I_{SD} = 20A, V_{GS} = 0V$			1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20A,		66		ns
Reverse Recovery Charge	Q <sub>rr</sub>	di <sub>F</sub> /dt = 100A/µs		73		nC

#### Notes

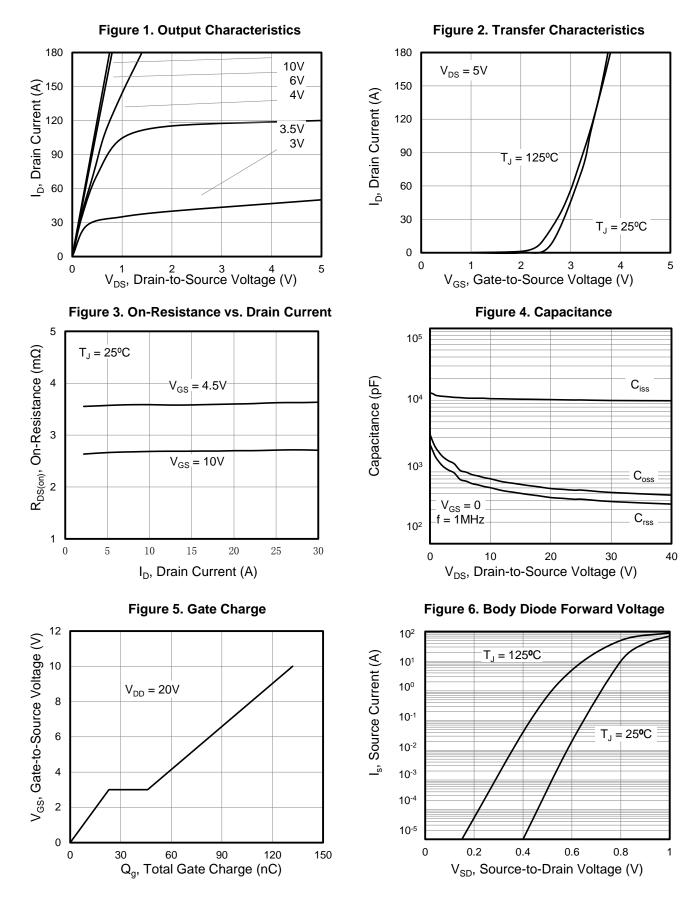
- 1. Repetitive Rating: Pulse Width limited by maximum junction temperature
- 2.  $V_{DD} = 40V$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^{\circ}C$
- 3. Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  1%



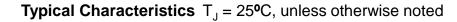
# TTD120N04AT, TTP120N04AT

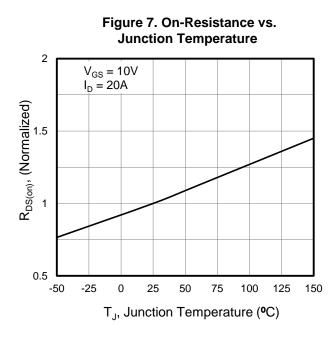
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### **Typical Characteristics** $T_J = 25^{\circ}C$ , unless otherwise noted









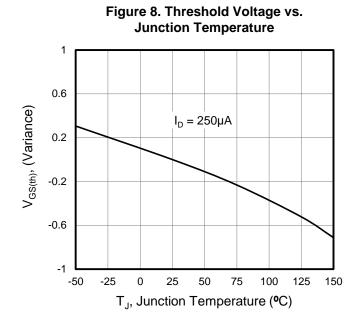
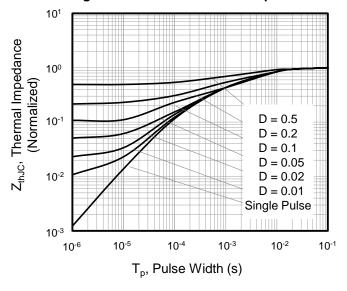
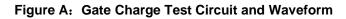
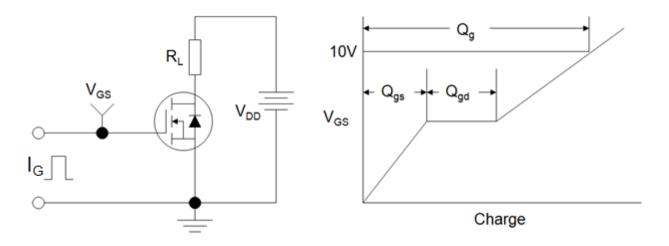


Figure 9. Transient Thermal Impedance









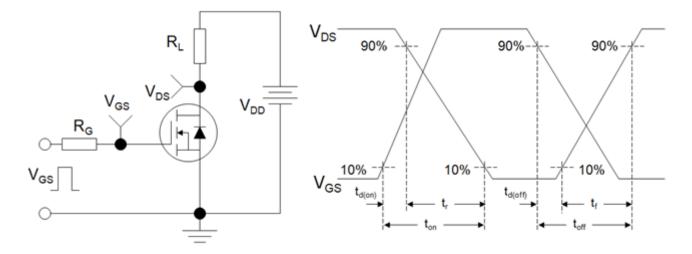
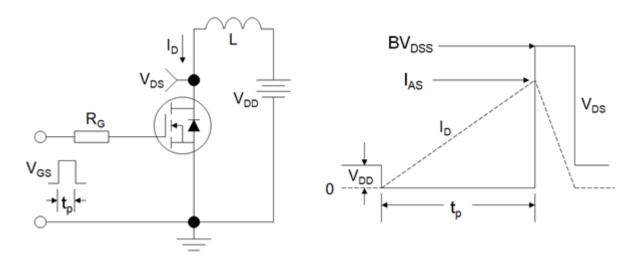
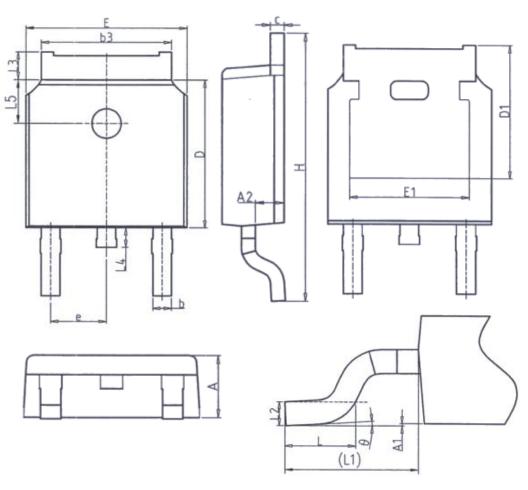


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





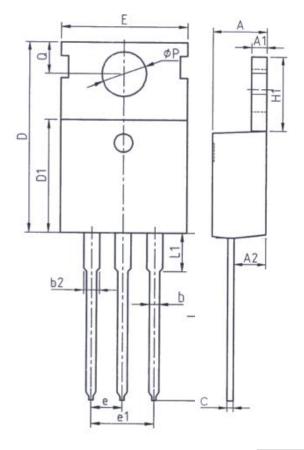
TO-252

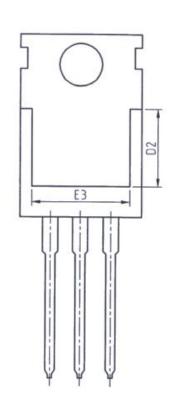


Unit: mm			
Symbol	Min.	Max.	
A	2.20	2.40	
A1	0.00	0.20	
A2	0.97	1.17	
b	0.68	0.90	
b3	5.20	5.50	
с	0.43	0.63	
D	5.98	6. 22	
D1	5. 30REF		
E	6.40	6.80	
E1	4.63	-	

Unit: mm			
Symbol	Min. Max.		
e	2. 286BSC		
Н	9.40	10.50	
L	1.38	1.75	
L1	2. 90REF		
L2	0. 51BSC		
L3	0.88	1.28	
L4	-	1.00	
L5	1.65	1.95	
θ	0°	8°	

**TO-220** 





Unit: mm			
Symbol	Min.	Max.	
Α	4.37	4.77	
A1	1.25	1.45	
A2	2.20	2.60	
b	0.70	0.95	
b2	1.17	1.47	
C	0.40	0.65	
D	15. 10	16. 10	
D1	8.80	9.40	
D2	5.50	-	

Unit: mm			
Symbol	Min.	Max.	
E	9.70	10. 30	
E3	7.00 -		
e	2. 54BSC		
e1	5. 08BSC		
H1	6. 25	6.85	
L	12.75	13.80	
L1	I	3. 40	
Р	3. 40	3.80	
Q	2.60	3.00	



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